T26 Standard Process

Chamber A (SiOx)

Wafer Size: 8 / 6 inch
Process Temperature: 400°C
Process RF Power: 270~300 Watt
Process Gas: SiH_4, N_2O
Recipe: 0.1 μm ~ 1 μm
Deposition Rate: > 400 nm/min

Chamber B (SiNx)

Wafer Size: 8 / 6 inch
Process Temperature: 400°C
Process RF Power: 850~890 Watt
Process Gas: SiH_4, N_2, NH_3
Recipe: 0.1 μm ~ 1 μm
Deposition Rate: > 150 nm/min